

WEST Search History

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<i>DB=USPT; PLUR=YES; OP=ADJ</i>			
<input type="checkbox"/>	L8	L2 and 510/\$.ccls.	24
<input type="checkbox"/>	L7	L2 and 134/\$.ccls.	19
<input type="checkbox"/>	L6	(5545353 or 5556482 or 4904571).pn.	3
<i>DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ</i>			
<input type="checkbox"/>	L5	L2 and carbamate	1
<input type="checkbox"/>	L4	L2 with carbamate	0
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<input type="checkbox"/>	L2	L1 with amines	151
<input type="checkbox"/>	L1	photoresist with removing	27902

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Search Results - Record(s) 1 through 10 of 19 returned.

☐ 1. Document ID: US 7056872 B2

L7: Entry 1 of 19

File: USPT

Jun 6, 2006

US-PAT-NO: 7056872

DOCUMENT-IDENTIFIER: US 7056872 B2

TITLE: Solution composition for removing a remaining photoresist resin

DATE-ISSUED: June 6, 2006

PRIOR-PUBLICATION:

DOC-ID

DATE

US 20030060382 A1

March 27, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Lee; Geun Su	Kyoungki-do			KR
Chung; Jae Chang	Kyoungki-Do			KR
Shin; Ki Soo	Kyoungki-do			KR
Oh; Kee Joon	Kyoungki-do			KR

US-CL-CURRENT: [510/175](#); [134/2](#), [134/3](#), [438/692](#), [510/176](#), [510/254](#), [510/255](#), [510/499](#)

ABSTRACT:

Cleaning solutions for removing photoresist resins remaining on the underlying layer patterns formed by photolithography process using the photoresist patterns as etching mask. The cleaning solution for removing photoresist comprises H.sub.2O as solvent, amine compounds, hydrazine hydrate, transition metal-removing material and alkali metal-removing material. Photoresist coated on the top portion of underlying layers can be rapidly and effectively removed by the disclosed cleaning solution. In addition, the cleaning solution is environment-friendly because H.sub.2O is used as the solvent, and has little effect on metal layers when underlying layers are formed of metals.

10 Claims, 5 Drawing figures

Exemplary Claim Number: 1

Number of Drawing Sheets: 3

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	RMK	Draw De
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☐ 2. Document ID: US 7049275 B2

L7: Entry 2 of 19

File: USPT

May 23, 2006

US-PAT-NO: 7049275

DOCUMENT-IDENTIFIER: US 7049275 B2

TITLE: Photoresist stripping composition and cleaning composition

DATE-ISSUED: May 23, 2006

PRIOR-PUBLICATION:

DOC-ID

DATE

US 20030181344 A1

September 25, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ikemoto; Kazuto	Tokyo			JP
Yamamoto; Yoshiaki	Niigata			JP
Yoshida; Hiroshi	Chiba			JP
Maruyama; Taketo	Chiba			JP

US-CL-CURRENT: 510/176; 134/1.3, 134/2, 510/175, 510/245, 510/255, 510/499

ABSTRACT:

The photoresist stripping composition of the present invention contains at least one oxymethylamine compound represented by the following formula 1: ##STR00001## wherein R.sup.1 to R.sup.3 are as defined in the specification. Of the oxymethylamine compound of the formula 1, the compound represented by the following formula 7: ##STR00002## wherein R.sup.2 to R.sup.5 and n are as defined in the specification, is a novel compound.

35 Claims, 2 Drawing figures

Exemplary Claim Number: 1

Number of Drawing Sheets: 2

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	Keywords	Drawings
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☐ 3. Document ID: US 7037852 B2

L7: Entry 3 of 19

File: USPT

May 2, 2006

US-PAT-NO: 7037852

DOCUMENT-IDENTIFIER: US 7037852 B2

TITLE: Composition for stripping photoresist and method of preparing the same

DATE-ISSUED: May 2, 2006

PRIOR-PUBLICATION:

INVENTOR-INFORMATION:

US-CL-CURRENT: 438/745; 134/1.2, 134/1.3, 252/79.1, 252/79.4, 257/E21.255, 438/749

A composition for stripping photoresist, methods of preparing and forming the same, a method of manufacturing a semiconductor device using the composition, and a method of removing a photoresist pattern from an underlying layer using the composition, where the composition may include an ethoxy N-hydroxyalkyl alkanamide represented by the formula, $\text{CH}_3\text{CH}_2\text{O}-\text{R}-\text{CO}-\text{N}-\text{R}_1\text{R}_2\text{OH}$, an alkanolamine and a polar material. Raw materials of alkyl alkoxy alkanate, represented by a chemical formula of $\text{R}_4\text{O}-\text{R}_3\text{COOR}_5$, and alkanolamine, represented by a chemical formula of $\text{NHR}_1\text{R}_2\text{OH}$, may be mixed to form a mixture, which is stirred and cooled to obtain the composition. The composition may balance exfoliation and dissolution of photoresist patterns, and may potentially eliminate thread-type residues from remaining on a surface of an underlying layer after removing the photoresist patterns.

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KnowC	Draw De
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Apr 5, 2005

DATE-ISSUED: April 5, 2005

INVENTOR-INFORMATION:

http://jupiter1:9000/bin/gate.exe?f=TOC&state=pmfu94.15&ref=7&dbname=USPT&ESNA... 9/20/07

Lin; Yu-Liang

Hsin-Chu

TW

US-CL-CURRENT: [438/781](#); [134/10](#), [134/12](#), [257/E21.242](#), [257/E21.259](#), [257/E21.262](#),
[257/E21.576](#), [438/782](#), [438/793](#)

ABSTRACT:

A method and apparatus for curing and modifying a low k dielectric layer in an interconnect structure is disclosed. A spin-on low k dielectric layer which includes an organic silsesquioxane, polyarylether, bisbenzocyclobuene, or SiLK is spin coated on a substrate. The substrate is placed in a process chamber in a supercritical CO.sub.2 system and is treated at a temperature between 30.degree. C. and 150.degree. C. and at a pressure from 70 to 700 atmospheres. A co-solvent such as CF.sub.3 --X or F--X is added that selectively replaces C--CH.sub.3 bonds with C--CF.sub.3 or C--F bonds. Alternatively, H.sub.2 O.sub.2 is employed as co-solvent to replace a halogen in a C--Z bond where Z=F, Cl, or Br with an hydroxyl group. Two co-solvents may be combined with CO.sub.2 for more flexibility. The cured dielectric layer has improved properties that include better adhesion, lower k value, increased hardness, and a higher elastic modulus.

78 Claims, 6 Drawing figures

Exemplary Claim Number: 1

Number of Drawing Sheets: 3

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw Da
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☐ 5. Document ID: US 6841526 B2

L7: Entry 5 of 19

File: USPT

Jan 11, 2005

US-PAT-NO: 6841526

DOCUMENT-IDENTIFIER: US 6841526 B2

**** See image for Certificate of Correction ****

TITLE: Cleaning solution for removing photoresist

DATE-ISSUED: January 11, 2005

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Lee; Geun Su	Kyoungki-do			KR
Jung; Jae Chang	Kyoungki-do			KR
Shin; Ki Soo	Seoul			KR

US-CL-CURRENT: [510/176](#); [134/2](#), [134/42](#), [430/331](#), [510/175](#), [510/255](#)

ABSTRACT:

Cleaning solutions for removing photoresist materials and a method of forming underlying layer patterns of semiconductor devices using the same. The cleaning solutions for removing photoresist include a solvent mixture of H.sub.2 O and an organic solvent, an amine compound, a transition metal-removing material and an alkali metal-removing material, and may further include a hydrazine hydrate.

17 Claims, 7 Drawing figures
Exemplary Claim Number: 1
Number of Drawing Sheets: 7

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KOMC	Draw De
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☐ 6. Document ID: US 6652666 B2

L7: Entry 6 of 19

File: USPT

Nov 25, 2003

US-PAT-NO: 6652666
DOCUMENT-IDENTIFIER: US 6652666 B2

TITLE: Wet dip method for photoresist and polymer stripping without buffer treatment step

DATE-ISSUED: November 25, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ma; Ching-Tien	Kaohsiung			TW
Shih; Chen-Hsi	Yung Kang			TW
Chen; Dian-Hau	Hsin-Chu			TW
Lu; Gau-Ming	Taipei			TW
Chen; Cho-Ching	Tainan			TW

US-CL-CURRENT: 134/30; 134/19, 134/38, 134/902, 257/E21.228, 257/E21.255

ABSTRACT:

A wet dip method for photoresist and polymer stripping from a wafer surface without the need for a buffer solvent treatment step is disclosed. In the method, the wafer is first exposed to an etchant solution that is maintained at a temperature of at least 80.degree. C. The wafer is then cooled in a room temperature air for a sufficient length of time until the temperature of the wafer reaches substantially room temperature. The wafer is then rinsed in a rinsing step that includes a quick dump rinse and a final rinse with deionized water that is maintained at a temperature not higher than room temperature without first exposing the wafer to a buffer solvent such as that required in a conventional wet dip method.

22 Claims, 2 Drawing figures
Exemplary Claim Number: 1
Number of Drawing Sheets: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KOMC	Draw De
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☐ 7. Document ID: US 6475292 B1

L7: Entry 7 of 19

File: USPT

Nov 5, 2002

US-PAT-NO: 6475292
DOCUMENT-IDENTIFIER: US 6475292 B1

TITLE: Photoresist stripping method

DATE-ISSUED: November 5, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Sahbari; Javad J.	Sunnyvale	CA		

US-CL-CURRENT: 134/3; 430/256

ABSTRACT:

A method for removing photoresist, probing ink and wafer bonding adhesive from a substrate using one or more (C.sub.6 -C.sub.16)olefins, one ore more (C.sub.1 - C.sub.6)alkoxybenzenes, and one ore more organic sulfonic acid compounds is provided.

13 Claims, 0 Drawing figures
Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Abstracts	Attachments	Claims	KWIC	Draw. De
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☐ 8. Document ID: US 6440647 B1

L7: Entry 8 of 19

File: USPT

Aug 27, 2002

US-PAT-NO: 6440647
DOCUMENT-IDENTIFIER: US 6440647 B1

TITLE: Resist stripping process

DATE-ISSUED: August 27, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Yakobson; Eric	Aliso Viejo	CA		

US-CL-CURRENT: 430/329; 134/1.3, 430/256, 430/258, 430/331, 510/175, 510/176

ABSTRACT:

A process for removing patterned negative working resist from the surface of a substrate during manufacture of printed wiring boards is disclosed. The process includes the steps of contacting the patterned resist with a stripping solution containing an alkalinity source as well as a source of ammonium ions. The stripping solution is characterized in that it does not contain volatile organic compounds (VOCs).

20 Claims, 0 Drawing figures

Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWMC	Draw De
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☐ 9. Document ID: US 6368421 B1

L7: Entry 9 of 19

File: USPT

Apr 9, 2002

US-PAT-NO: 6368421

DOCUMENT-IDENTIFIER: US 6368421 B1

TITLE: Composition for stripping photoresist and organic materials from substrate surfaces

DATE-ISSUED: April 9, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Oberlander; Joseph E.	Phillipsburg	NJ		
Slezak; Mark S.	Sunnyvale	CA		
Khanna; Dinesh N.	Flemington	NJ		
Durham; Dana L.	Flemington	NJ		
Spinicelli; Lawrence F.	Matthews	NC		

US-CL-CURRENT: 134/40; 134/38, 134/39, 510/175, 510/176, 510/365

ABSTRACT:

The invention relates to the field of microelectronics, such as integrated circuits, and more particularly to compositions and methods of removing photoresists or other organic materials from the surfaces of substrates used in the fabrication of integrated circuits. In particular the present invention relates to amine-free stripping compositions comprising solvent and surfactant that can effectively remove organic materials without corroding the underlying substrate, and the invention also relates to methods for removing these organic materials with the novel stripping composition.

10 Claims, 0 Drawing figures

Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWMC	Draw De
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☐ 10. Document ID: US 6276372 B1

L7: Entry 10 of 19

File: USPT

Aug 21, 2001

US-PAT-NO: 6276372

DOCUMENT-IDENTIFIER: US 6276372 B1

TITLE: Process using hydroxylamine-gallic acid composition

DATE-ISSUED: August 21, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Lee; Wai Mun	Fremont	CA		

US-CL-CURRENT: 134/1.3; 134/2, 134/39, 257/E21.255, 257/E21.577, 257/E21.589,
510/175, 510/176, 510/245, 510/254, 510/477, 510/488, 510/499, 510/505

ABSTRACT:

A hydroxylamine-gallic compound composition comprises a hydroxylamine compound, at least one alcohol amine compound which is miscible with the hydroxylamine compound and a gallic compound. A process for removing photoresist or other polymeric material or a residue from a substrate, such as an integrated circuit semiconductor wafer including titanium metallurgy, in accordance with this invention comprises contacting the substrate with a hydroxylamine compound, an alcohol amine compound which is miscible with the hydroxylamine compound and a gallic compound for a time and at a temperature sufficient to remove the photoresist, other polymeric material or residue from the substrate. Use of a gallic compound in place of catechol in the composition and process reduces attack on titanium metallurgy by, e.g., about three times.

6 Claims, 34 Drawing figures

Exemplary Claim Number: 1

Number of Drawing Sheets: 34

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	RMK	Draw De
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"134/102.1"	512
"134/102.2"	236
"134/102.3"	135
"134/103.1"	254
"134/103.2"	313
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☐ 11. Document ID: US 6150282 A

L7: Entry 11 of 19

File: USPT

Nov 21, 2000

US-PAT-NO: 6150282

DOCUMENT-IDENTIFIER: US 6150282 A

TITLE: Selective removal of etching residues

DATE-ISSUED: November 21, 2000

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Rath; David L.	Stormville	NY		
Jagannathan; Rangarajan	Essex Junction	VT		
McCullough; Kenneth J.	Fishkill	NY		
Okorn-Schmidt; Harald F.	Putnam Valley	NY		
Madden; Karen P.	Poughquag	NY		
Pope; Keith R.	Danbury	CT		

US-CL-CURRENT: 438/745; 134/2, 134/3, 257/E21.228, 257/E21.577, 438/906

ABSTRACT:

Etching residue is selectively removed employing a substantially non-aqueous composition containing a fluoride containing compound and certain organic solvents. Preferred compositions also include an anhydride.

40 Claims, 0 Drawing figures

Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KOMC	Draw De
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☐ 12. Document ID: US 5753601 A

L7: Entry 12 of 19

File: USPT

May 19, 1998

US-PAT-NO: 5753601

DOCUMENT-IDENTIFIER: US 5753601 A

TITLE: Organic stripping composition

Display Format:

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DATE-ISSUED: May 19, 1998

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ward; Irl E.	Bethlehem	PA		
Michelotti; Francis W.	Easton	PA		

US-CL-CURRENT: 510/176; 134/2, 134/38, 134/40, 510/401

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

1 Claims, 0 Drawing figures
Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMMC	Draw De
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☐ 13. Document ID: US 5707947 A

L7: Entry 13 of 19

File: USPT

Jan 13, 1998

US-PAT-NO: 5707947

DOCUMENT-IDENTIFIER: US 5707947 A

TITLE: Organic stripping composition

DATE-ISSUED: January 13, 1998

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ward; Irl E.	Bethlehem	PA		
Michelotti; Francis W.	Easton	PA		

US-CL-CURRENT: 510/176; 134/2, 134/38, 134/40, 510/175, 510/255, 510/401, 510/402, 510/405, 510/499, 510/505

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

1 Claims, 0 Drawing figures
Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMMC	Draw De
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☐ 14. Document ID: US 5648324 A

L7: Entry 14 of 19

File: USPT

Jul 15, 1997

US-PAT-NO: 5648324

DOCUMENT-IDENTIFIER: US 5648324 A

TITLE: Photoresist stripping composition

DATE-ISSUED: July 15, 1997

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Honda; Kenji	Barrington	RI		
Perry; Donald F.	North Providence	RI		
Maw; Taishih	Cumberland	RI		

US-CL-CURRENT: 510/176; 134/38, 252/394, 510/255, 510/500

ABSTRACT:

A photoresist stripping composition containing:

(a) 20-70% by weight of an organic polar solvent having a dipole moment of more than 3.5;

(b) 70-20% by weight of alkanolamine compounds; and

(c) 0.1-10% by weight of 2,2'[[methyl-1H-benzothiazol-1-yl)methyl]imino]bis-ethanol.

4 Claims, 0 Drawing figures

Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	RM/C	Draw De
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☐ 15. Document ID: US 5556482 A

L7: Entry 15 of 19

File: USPT

Sep 17, 1996

US-PAT-NO: 5556482

DOCUMENT-IDENTIFIER: US 5556482 A

TITLE: Method of stripping photoresist with composition containing inhibitor

DATE-ISSUED: September 17, 1996

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ward; Irl E.	Bethlehem	PA		
Michelotti; Francis W.	Easton	PA		

US-CL-CURRENT: 134/38; 134/2, 134/40, 510/176, 510/401, 510/402

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

1 Claims, 0 Drawing figures

Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWOC	Draw De
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☐ 16. Document ID: US 5496491 A

L7: Entry 16 of 19

File: USPT

Mar 5, 1996

US-PAT-NO: 5496491

DOCUMENT-IDENTIFIER: US 5496491 A

TITLE: Organic stripping composition

DATE-ISSUED: March 5, 1996

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ward, Irl E.	Bethlehem	PA		
Michelotti, Francis W.	Easton	PA		

US-CL-CURRENT: 510/176; 134/38, 252/364, 252/393, 252/394, 252/395, 252/396, 510/202, 510/212

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

12 Claims, 0 Drawing figures

Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWOC	Draw De
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☐ 17. Document ID: US 5480585 A

L7: Entry 17 of 19

File: USPT

Jan 2, 1996

US-PAT-NO: 5480585

DOCUMENT-IDENTIFIER: US 5480585 A

TITLE: Stripping liquid compositions

DATE-ISSUED: January 2, 1996

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Shiotsu; Shinichiro	Hyogo			JP
Horiuchi; Yoshiaki	Horiuchi			JP

US-CL-CURRENT: 510/176; 134/38, 257/E21.255, 430/329, 510/202, 510/212, 510/407,
510/493, 510/505

ABSTRACT:

A photoresist stripping liquid composition comprising an alkanol amine compound, a sulfone compound or sulfoxide compound, and a hydroxy compound. The composition is excellent in its photoresist stripping performance, safety and working efficiency, and does not cause corrosion on a substrate possessing a metal film.

6 Claims, 0 Drawing figures
Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KUMC	Draw De
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☐ 18. Document ID: US 5417877 A

L7: Entry 18 of 19

File: USPT

May 23, 1995

US-PAT-NO: 5417877

DOCUMENT-IDENTIFIER: US 5417877 A

TITLE: Organic stripping composition

DATE-ISSUED: May 23, 1995

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ward; Irl E.	Hatfield	PA		

US-CL-CURRENT: 510/176; 134/38, 252/364, 510/202, 510/206, 510/212, 510/255,
510/265, 510/500

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

12 Claims, 0 Drawing figures
Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw D
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☐ 19. Document ID: US 5399202 A

L7: Entry 19 of 19

File: USPT

Mar 21, 1995

US-PAT-NO: 5399202

DOCUMENT-IDENTIFIER: US 5399202 A

TITLE: Resist-peeling liquid and process for peeling a resist using the same

DATE-ISSUED: March 21, 1995

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kikuchi; Hiroshi	Zushi			JP
Sano; Yasushi	Yokohama			JP
Todoroki; Satoru	Yokohama			JP
Oka; Hitoshi	Yokohama			JP
Koshita; Toshiyuki	Mobara			JP
Kikuchi; Masato	Mobara			JP
Nakatani; Mitsuo	Mobara			JP
Tsukii; Michio	Mobara			JP

US-CL-CURRENT: 134/1; 134/38, 510/176, 510/202, 510/212

ABSTRACT:

A resist is peeled without leaving a residue after peeling, by bringing a resist-peeling liquid comprising a primary aliphatic amine of 2-6 carbon atoms into contact with the surface of an etched novolak positive photoresist, and removing the resist-peeling liquid containing the thus peeled resist from the surface of the etched resist. The used resist-peeling liquid can easily be recovered and regenerated.

8 Claims, 10 Drawing figures

Exemplary Claim Number: 1

Number of Drawing Sheets: 5

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw D
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134/\$	0
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"134/102.2"	236
"134/102.3"	135
"134/103.1"	254
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"134/103.3"	57
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